

Application

These 1N4153-1 switching diodes are small signal diodes particularly designed for general purpose switching and demodulation applications.

Features

- METALLURGICALLY BONDED
- FAST FORWARD AND REVERSE RECOVERY TIME
- LOW FORWARD RECOVERY VOLTAGE
- LOW CAPACITANCE AT HIGH FREQUENCIES
- PLANAR PASSIVATED CHIP
- AVAILABLE IN JAN, JANTX, AND JANTXV QUALIFICATIONS TO MIL-S-19500/337

Maximum Ratings @ 25°C

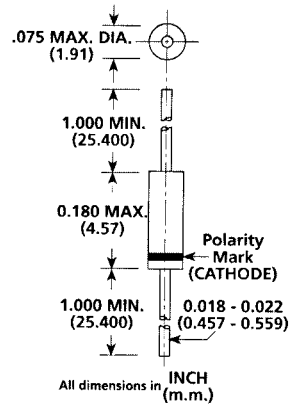
- Reverse Breakdown Voltage: 75V
- Peak Working Voltage: 50V
- Average Output Current: 150 mA dc
- Forward Surge Current, 1 μ s: 2.0A
- Average Current Derating: 1.00 mA/°C above 25°C
- Operating Temperature Range: -65°C to +175°C
- Storage Temperature Range: -65°C to +175°C
- Thermal Impedance, 10ms: 50°C/w at 10ms
- Thermal Resistance, (at lead length of 0.375"): 250°C/w

Electrical Characteristics @ 25°C

Limit	V _{F1} I _F = 100 μ A dc	V _{F2} I _F = 250 μ A dc	V _{F3} I _F = 1 mA dc	V _{F4} I _F = 2 mA dc	V _{F5} I _F = 10 mA dc	V _{F6} I _F = 20 mA dc
Min.	0.490 V dc	0.530 V dc	0.590 V dc	0.620 V dc	0.700 V dc	0.740 V dc
Max.	0.550 V dc	0.590 V dc	0.670 V dc	0.700 V dc	0.810 V dc	0.880 V dc

Limit	I _{R1} V _R = 50 V dc	I _{R2} V _R = 50 V dc T _A = 150°C	C V _R = 0 V dc F = 1 MHZ	t _{rr} I _F = I _R = 10 mA dc R _L = 100 ohms, I _{RR} = 1.0 mA dc
Min.	---	---	---	---
Max.	50 nA dc	50 μ A dc	2.0 pF	4 ns

PACKAGE DIMENSIONS



Mechanical Characteristics

CASE: Hermetically Sealed Glass Case DO-35.

FINISH: All External Surfaces Are Corrosion Resistant And Leads Solderable.

POLARITY: Banded End Is Cathode.

WEIGHT: 0.2 Grams.